

insulating layer therebetween,

wherein said channel semiconductor layer comprises a non-single crystalline silicon semiconductor layer containing oxygen, nitrogen or carbon at a concentration 5×10^{19} atoms/cm³ or less and a peak intensity ratio I_a/I_c of said channel semiconductor layer is less than 0.4 (where I_a represents a Raman peak intensity at a wavenumber of 480cm⁻¹ for an amorphous component of said channel semiconductor layer and I_c represents a Raman peak intensity at 521 cm⁻¹ for a single crystalline silicon.


28. The thin film transistor of claim 27 wherein said channel semiconductor layer is formed on an insulating surface of a substrate.--

REMARKS

Claims 1-4 and 15-22 have been cancelled and new claims 23-28 have been added to provide a more complete scope of coverage.

Examination on the merits is requested.

Respectfully submitted,


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